
**Microbeam analysis — Scanning
electron microscopy — Vocabulary**

*Analyse par microfaisceaux — Microscopie électronique à balayage
— Vocabulaire*

STANDARDSISO.COM : Click to view the full PDF of ISO 22493:2014



STANDARDSISO.COM : Click to view the full PDF of ISO 22493:2014



COPYRIGHT PROTECTED DOCUMENT

© ISO 2014

All rights reserved. Unless otherwise specified, no part of this publication may be reproduced or utilized otherwise in any form or by any means, electronic or mechanical, including photocopying, or posting on the internet or an intranet, without prior written permission. Permission can be requested from either ISO at the address below or ISO's member body in the country of the requester.

ISO copyright office
Case postale 56 • CH-1211 Geneva 20
Tel. + 41 22 749 01 11
Fax + 41 22 749 09 47
E-mail copyright@iso.org
Web www.iso.org

Published in Switzerland

Contents

	Page
Foreword.....	iv
Introduction.....	v
1 Scope.....	1
2 Abbreviated terms.....	1
3 Terms and definitions used in the physical basis of SEM.....	1
4 Terms and definitions used in SEM instrumentation.....	5
5 Terms and definitions used in SEM image formation and processing.....	12
6 Terms and definitions used in SEM image interpretation and analysis.....	16
7 Terms and definitions used in the measurement and calibration of SEM image magnification and resolution.....	18
Bibliography.....	20

STANDARDSISO.COM : Click to view the full PDF of ISO 22493:2014

Foreword

ISO (the International Organization for Standardization) is a worldwide federation of national standards bodies (ISO member bodies). The work of preparing International Standards is normally carried out through ISO technical committees. Each member body interested in a subject for which a technical committee has been established has the right to be represented on that committee. International organizations, governmental and non-governmental, in liaison with ISO, also take part in the work. ISO collaborates closely with the International Electrotechnical Commission (IEC) on all matters of electrotechnical standardization.

The procedures used to develop this document and those intended for its further maintenance are described in the ISO/IEC Directives, Part 1. In particular the different approval criteria needed for the different types of ISO documents should be noted. This document was drafted in accordance with the editorial rules of the ISO/IEC Directives, Part 2 (see www.iso.org/directives).

Attention is drawn to the possibility that some of the elements of this document may be the subject of patent rights. ISO shall not be held responsible for identifying any or all such patent rights. Details of any patent rights identified during the development of the document will be in the Introduction and/or on the ISO list of patent declarations received (see www.iso.org/patents).

Any trade name used in this document is information given for the convenience of users and does not constitute an endorsement.

For an explanation on the meaning of ISO specific terms and expressions related to conformity assessment, as well as information about ISO's adherence to the WTO principles in the Technical Barriers to Trade (TBT) see the following URL: Foreword - Supplementary information

The committee responsible for this document is ISO/TC 202, *Microbeam analysis*, Subcommittee SC 1, *Terminology*.

This second edition cancels and replaces the first edition (ISO 22493:2008), of which it constitutes a minor revision.

Introduction

The scanning electron microscopy (SEM) technique is used to observe and characterize the surface morphology and structure of solid materials, such as metal alloys, ceramics, glasses, minerals, polymers, powders, etc., on a spatial scale of micrometer down to nanometer laterally. In addition, three-dimensional structure can be generated by using a combination of focused ion beam and scanning-electron-based analysis techniques. The SEM technique is based on the physical mechanism of electron optics, electron scattering and secondary electron emission.

As a major sub-field of microbeam analysis (MBA), the SEM technique is widely applied in diverse sectors (high-tech industries, basic industries, metallurgy and geology, biology and medicine, environmental protection, trade, etc.) and has a strong business base that needs standardization.

Standardizing the terminology of a technical field is one of the basic prerequisites for development of standards on other aspects of that field.

This International Standard is relevant to the need for an SEM terminology that contains consistent definitions of terms as they are used in the practice of scanning electron microscopy by the international scientific and engineering communities that employ the technique. This International Standard is the second one developed in a package of standards on electron probe microanalysis (EPMA), scanning electron microscopy (SEM), analytical electron microscopy (AEM), energy-dispersive X-ray spectroscopy (EDS), etc., developed or to be developed by Technical Committee ISO/TC 202, *Microbeam analysis*, Subcommittee SC 1, *Terminology*, to cover the complete field of MBA.

STANDARDSISO.COM : Click to view the full PDF of ISO 22493:2014

[STANDARDSISO.COM](https://standardsiso.com) : Click to view the full PDF of ISO 22493:2014

Microbeam analysis — Scanning electron microscopy — Vocabulary

1 Scope

This International Standard defines terms used in the practice of scanning electron microscopy (SEM). It covers both general and specific concepts, classified according to their hierarchy in a systematic order, with those terms that have already been defined in ISO 23833 also included, where appropriate.

This International Standard is applicable to all standardization documents relevant to the practice of SEM. In addition, some clauses of this International Standard are applicable to documents relevant to related fields (e.g. EPMA, AEM, EDS) for the definition of terms which are relevant to such fields.

2 Abbreviated terms

AEM	analytical electron microscope/microscopy
BSE (BE)	backscattered electron
CPSEM	controlled pressure scanning electron microscope/microscopy
CRT	cathode ray tube
EBIC	electron beam induced current
EBSD	electron backscatter/backscattering diffraction
EDS	energy-dispersive spectrometer/spectrometry
EPMA	electron probe microanalyser/analysis
ESEM	environmental scanning electron microscope/microscopy
FWHM	full width at half maximum
SE	secondary electron
SEM	scanning electron microscope/microscopy
VPSEM	variable-pressure scanning electron microscope/microscopy

3 Terms and definitions used in the physical basis of SEM

3.1

electron optics

science that deals with the passage of electrons through electrostatic and/or electromagnetic fields

3.1.1

electron source

device that generates electrons necessary for forming an electron beam in the electron optical system

3.1.1.1

energy spread

diversity of energy of electrons

3.1.1.2

effective source size

effective dimension of the electron source

3.1.2

electron emission

ejection of electrons from the surface of a material under given excitation conditions

3.1.2.1

field emission

electron emission caused by the strong electric field on and near the surface of a material

3.1.2.1.1

cold field emission

field emission in which the emission process relies purely on the high-strength electrostatic field in a high-vacuum environment with the cathode operating at ambient temperature

3.1.2.1.2

thermal field emission

Schottky emission

field emission in which the emission process relies on both the elevated temperature of the cathode tip and an applied electric field of high voltage in a high-vacuum environment

3.1.2.2

thermionic emission

electron emission that relies on the use of high temperature to enable electrons in the cathode to overcome the work function energy barrier and escape into the vacuum

3.1.3

electron lens

basic component of an electron optical system, using an electrostatic and/or electromagnetic field to change the trajectories of the electrons passing through it

3.1.3.1

electrostatic lens

electron lens employing an electrostatic field formed by a specific configuration of electrodes

3.1.3.2

electromagnetic lens

electron lens employing an electromagnetic field formed by a specific configuration of electromagnetic coil (or permanent magnet) and pole piece

3.1.4

focusing

aiming the electrons onto a particular point using an electron lens

3.1.5

demagnification

numerical value by which the diameter of the electron beam exiting a lens is reduced in comparison to the diameter of the electron beam entering the lens

3.2

electron scattering

electron deflection and/or its kinetic energy loss as a result of collision(s) with target atom(s) or electron(s)

3.2.1

elastic scattering

electron scattering in which energy and momentum are conserved in the collision system

3.2.1.1**backscattering**

electron scattering in which the incident electrons scatter backwards and out of the target after suffering deflections

3.2.2**inelastic scattering**

electron scattering in which energy and/or momentum are not conserved in the collision system

Note 1 to entry: For inelastic scattering, the electron trajectory is modified by a small angle, generally less than 0,01 rad.

3.2.3**scattering cross-section**

hypothetical area normal to the incident radiation that would geometrically intercept the total amount of radiation actually scattered by a scattering particle

Note 1 to entry: Scattering cross-section is usually expressed only as area (m²).

3.2.4**mean free path**

mean distance between electron scattering events in any material

3.2.5**Bethe range**

estimate of the total distance an electron can travel in any material (including vacuum and a target), obtained by integrating the Bethe stopping power equation over the energy range from the incident value to a low threshold value (e.g. 1 keV)

Note 1 to entry: This assumes that the electron loses energy continuously in the material rather than as occurs in practice where energy is lost in discrete scattering events.

3.3**backscattered electron****BSE**

electron ejected from the entrance surface of the specimen by the backscattering process

Note 1 to entry: By convention, an electron ejected with an energy greater than 50 eV may be considered as a backscattered electron.

3.3.1**backscattering coefficient****BSE yield**

η

ratio of the total number of backscattered electrons to the total number of incident electrons

3.3.2**BSE angular distribution**

distribution of backscattered electrons as a function of their emitting angle relative to the specimen surface normal

3.3.3**BSE atomic number dependence**

variation of backscattering coefficient as a function of the atomic number of the specimen

3.3.4**BSE beam energy dependence**

variation of backscattering coefficient with beam energy

3.3.5

BSE depth distribution

distribution describing the locations of the electrons at their maximum depth in the specimen before subsequently being backscattered from the specimen surface

3.3.6

BSE energy distribution

distribution of backscattered electrons as a function of their emitting energy

3.3.7

BSE escape depth

maximum depth in a specimen from which a backscattered electron may emerge

3.3.8

BSE lateral spatial distribution

two-dimensional distribution of backscattered electrons escaping as a function of the distance from the beam impact point to the lateral position of escape

3.4

secondary electron

electron emitted from a specimen as a result of bombardment by the primary electrons

Note 1 to entry: By convention, an electron with energy less than 50 eV is considered as a secondary electron.

3.4.1

SE yield

secondary electron coefficient

total number of secondary electrons per incident electron

3.4.2

SE angular distribution

distribution of secondary electrons as a function of their emitting angle relative to the surface normal

3.4.3

SE energy distribution

distribution of secondary electrons as a function of their emitting energy

3.4.4

SE escape depth

maximum depth under a surface from which secondary electrons are emitted

3.4.5

SE tilt dependence

effect on secondary electrons of the specimen tilt which accompanies a change in incident beam angle

3.4.6

SE₁ (SE_I)

secondary electrons that are generated by the incident beam electrons within the specimen

3.4.7

SE₂ (SE_{II})

secondary electrons that are generated by the backscattered electrons within the specimen

3.4.8

SE₃ (SE_{III})

secondary electrons that are generated by the electrons backscattered from the specimen somewhere remotely beyond the point of incidence

3.4.9**SE₄ (SE_{IV})**

secondary electrons that are generated by the incident beam electrons within the electron optical column

3.5**electron penetration**

physical process of forwards travelling by an energetic incident beam electron before losing all its energy within the target (specimen)

3.5.1**electron range**

measure of the straight-line penetration distance of electrons in a solid

3.5.2**interaction volume**

volume below the incident electron beam impact area at the specimen surface, within which the beam electrons travel and experience elastic and inelastic scattering

3.5.3**information volume**

volume of the specimen from which the measured signal originates

3.5.4**penetration depth**

depth to which an incident electron travels in a target

3.5.5**Monte Carlo simulation**

calculation that simulates stochastic physical processes (here: the electron diffusion in the solid state) and thus can be used to model the electron probe - sample interaction and SEM image formation

3.6**electron channelling**

physical process occurring in crystalline materials of greater electron penetration along directions of low atomic density

3.7**electron diffraction**

physical process of particularly strong scattering of the incident electron beam at certain angles relative to the atomic planes in a crystal

3.7.1**electron backscattering diffraction****EBSD**

diffracting process that arises between the backscattered electrons and the atomic planes of a specimen illuminated by the incident electron beam

4 Terms and definitions used in SEM instrumentation**4.1****electron gun**

component that produces an electron beam with a well-defined kinetic energy

4.1.1**field emission gun**

electron gun employing field emission

4.1.1.1

cold field emission gun

electron gun employing cold field emission

4.1.1.1.1

extracting electrode

electrode applying the electrostatic potential to extract electrons from the electron source

4.1.1.1.2

flashing

short-time heating process usually applied to a cold field emission gun to clean the surface of the electron source tip

4.1.1.2

thermal field emission gun

electron gun employing thermal field emission

4.1.2

thermionic emission gun

electron gun employing thermionic emission

4.1.2.1

tungsten hairpin gun

thermionic emission gun employing a tungsten hairpin filament as its cathode

4.1.2.2

LaB₆ gun

thermionic emission gun employing a heated block of single-crystal LaB₆ as its cathode

4.1.2.3

anode

one of the electrodes making up the electron gun, to which a high positive voltage relative to the cathode is applied to accelerate the emitted electrons from the cathode

4.1.2.4

cathode

one of the electrodes making up the electron gun, which is at a negative electric potential relative to the anode

4.1.2.5

Wehnelt cylinder

cap-shaped electrode, placed between anode and cathode in the electron gun, which acts to focus electrons inside the gun and to control the amount of electron emission

4.1.3

brightness

β

current per unit area at the focus position and per unit solid angle in the beam

Note 1 to entry: Brightness is given by the equation

$$\beta = 4I/(\pi^2 d^2 \alpha^2)$$

where

I is the current, in amperes;

d is the beam diameter, in metres, at the focus position;

α is the beam half-angle, in radians.

4.1.4 reduced brightness

β'
brightness (beam current density) normalized to the beam acceleration voltage

Note 1 to entry: Reduced brightness is given by the equation

$$\beta' = \beta/V$$

where

β is the measured brightness;

V is the electron beam acceleration voltage.

4.1.5 emission current

total electron current emitted from the cathode

4.1.6 saturation

specific cathode heating condition at which a change in the cathode heating current will result in only a small change in the electron beam current, which is close to its maximum

4.2 electron lens system

combination of various electron lenses to obtain specific electron optics functions

4.2.1 aberration

divergence from ideal properties of an electron optical element, e.g. lens imperfections like spherical aberration, chromatic aberration, diffraction, that degrade the lens optical performance

4.2.1.1 chromatic aberration

lens defect that arises because electrons from the same point but of slightly different energies will be focused at different positions in the image plane

4.2.1.2 spherical aberration

lens defect which arises because electrons in trajectories further away from the optic axis are bent more strongly by the lens magnetic field than those near the axis

4.2.2 aperture

diaphragm with an axial opening that defines the transmission of the lens

4.2.2.1 aperture angle

half of the angle subtended by the diameter of the aperture at the point of beam focus

4.2.2.2 aperture diffraction

defect that arises at very small aperture diameters because the wave nature of electrons gives rise to a diffraction pattern instead of a point in the Gaussian image plane

4.2.2.3 objective aperture

aperture that restricts the cross-sectional area of the electron beam incident on the specimen

4.2.2.4

virtual objective aperture

beam-limiting aperture located between the last condenser and the objective lens

4.2.3

astigmatism

phenomenon in which electrons emerging from a point object are focused to form two separate focal lines at 90° to one another rather than a point focus as formed by a perfectly cylindrical lens

Note 1 to entry: It arises from the lens asymmetrical magnetic field caused by machining errors, inhomogeneities in the pole pieces, asymmetry in the lens windings and imperfect apertures.

4.2.3.1

stigmator

device that applies weak supplementary magnetic fields to correct astigmatism

4.2.4

condenser lens

electron optical device used to converge or diverge transmitted electrons

Note 1 to entry: The principal function of the condenser is to set the beam current and control its three-dimensional shape.

4.2.5

objective lens

lens in a microscope closest to the specimen

Note 1 to entry: The principal function of the objective lens is to focus the final probe.

4.2.5.1

conical lens

objective lens in the shape of a cone pointing towards the specimen

4.2.5.2

immersion lens

electron lens in which the object lies deep within the electric field so that the lens field varies rapidly in its vicinity

4.2.5.3

snorkel lens

objective lens of asymmetric single-pole configuration with the ability to accommodate large specimens, with low aberrations and with flexibility for through-lens electron detection and imaging

4.3

scanning system

device incorporated in the electron optical system for achieving time-controlled one- or two-dimensional movement of the electron probe on the specimen surface and synchronized signal collection to generate line scans or images

4.3.1

analogue scanning system

scanning system with an analogue circuit as its scanning signal source, in which the electron probe is moved continuously, with a rapid scan along the x -axis (the line scan) and a slower scan at right angles along the y -axis (the frame scan), so that a good approximation to an orthogonal scan is produced

4.3.2

digital scanning system

scanning system, with a digital circuit as its scanning signal source, in which the electron probe is moved discretely from a point being addressed to a particular location (x, y) in a matrix, remains there for a fixed time (the dwell time) and is then moved to the next data collection point

4.3.3**double deflection**

action of deflecting the electron beam at first off-axis and then to cross the optical axis again at the final (beam defining) aperture

4.3.4**dwelt time**

time during which the electron probe stays in a particular location in digital scanning operation

4.4**specimen chamber**

compartment just next to the objective lens where the specimen stage with specimen is accommodated and manipulated

4.4.1**charge balance**

condition at which the number of incident electrons impinging on the specimen surface equals the number of electrons (secondary, backscattered, etc.) leaving the specimen

4.4.2**differential pumping**

pumping method designed to achieve and maintain the different vacuum values for chambers connected by diaphragms which prevent the exchange of large amounts of gas

4.4.3**gas path length**

average distance electrons pass through gas to reach the specimen

4.4.4**gas amplification**

effect of multiple ionization events leading to secondary electron cascade due to electron-gas interaction under an applied electric field leading to a signal gain

4.4.5**CPSEM****controlled pressure SEM**

variable pressure SEM

VPSEM

environmental SEM

ESEM

controlled pressure SEM which can operate with a pressure in the specimen chamber from 1 Pa up to 5 000 Pa so that direct secondary emission is no longer detectable and images are obtained with the detection of electrons by *gas amplification* (4.4.4), *environmental SE detector* (4.6.2.6), ions, photoemission or using other signals such as BSE or absorbed current

Note 1 to entry: This type of SEM can be also used with a normal vacuum in the chamber.

4.5**specimen**

sampled material designated to be examined or analysed

4.5.1**specimen stage**

device, located in the specimen chamber, which enables the specimen to be appropriately mounted, manipulated and held in place

Note 1 to entry: It usually allows for some of the five degrees of freedom in motion, i.e. *x-y-z* displacements, tilting and rotating.

4.5.2

working distance

distance between the lower surface of the pole piece of the objective lens and the specimen surface

Note 1 to entry: In the past, this distance was defined as the distance between the principal plane of the objective lens and the plane containing the specimen surface.

4.5.3

contamination

extraneous surface layer on the specimen surface and/or localized build-up of foreign material on the surface arising from electron beam bombardment

4.5.4

coating

procedure of covering the specimen surface with a thin layer of material (usually conductive) which is generally created by vacuum evaporation or sputtering

4.5.5

edge effect

signal enhancement at edge features of the specimen surface in SEM images

4.6

signal detection

collection of the physical signals generated by the electron-specimen interaction and their conversion into electronic signals for further processing

4.6.1

detector

device employed to achieve signal collection and conversion into an electronic signal

4.6.2

electron detector

detector specifically designed for collection of electrons and their conversion into an electronic signal

4.6.2.1

BSE to SE conversion detector

version of the Everhart-Thornley detector for the collection of BSE signals through collection of remotely generated SEs by the use of a specific electrode having a high BSE to SE conversion efficiency

4.6.2.2

EBSD CCD-based camera

detector system, used for imaging of EBSD patterns, which involves a fluorescent screen, an optical camera lens system, a charge-coupled device and a computer to collect the data

4.6.2.3

IR camera

detector system used to observe the contents of the specimen chamber with infra-red light

4.6.2.4

channel plate detector

SE and BSE detector for all energy range operation and multiplication occurring within the capillaries through the detector plate with an accelerating potential applied between the exit and the entrance faces

4.6.2.5

combined scintillator/light guide BSE detector

dedicated BSE detector in which a large-area scintillator (made of the same material as the light guide) is placed above the specimen surface, close to and symmetrical with the surface, to achieve BSE collection over a solid angle of nearly 2π

4.6.2.6**environmental SE detector
gas (or gaseous) SE detector**

special type of SE detector, dedicated to VPSEM or CPSEM, which operates on the principle of amplified ion signal current generated in the SE-gas ionization process by the accelerated SEs in the presence of an electric field produced by positively biasing an electrode near the specimen placed in a gaseous environment

4.6.2.7**Everhart-Thornley detector**

type of SE detector named after its designers T. Everhart and R.F.M. Thornley

Note 1 to entry: The basic component of the detector is a scintillator that emits photons when hit by high-energy electrons. The emitted photons are collected by a light guide and transported to a photomultiplier for detection.

4.6.2.8**solid-state diode detector**

dedicated BSE detector which operates on the principle of electron-hole production induced in a semiconductor by energetic electrons, with the features of flexible configuration, large solid angle, multiple arrays, energy selectivity and self-amplification

4.6.2.9**through-the-lens (TTL) detector**

special kind of SE/BSE detector, adapted to the objective lens, in which the SEs/BSEs emitted from the specimen spiral up along the lens magnetic field, pass up through the lens bore and are collected by electron detector(s) placed on one side of the column

4.6.2.10**in-lens detector**

special kind of SE/BSE detector, placed between the pole pieces of the objective lens, in which the SEs/BSEs emitted from the specimen spiral up along the lens magnetic field, pass up through the lens bore and are collected by electron detector(s) coaxial with the beam

4.6.3**take-off angle**

angle between the surface of the specimen and the line connecting the beam impact point on the specimen surface to the centre of the detector face

Note 1 to entry: In this instance, the term does not apply to X-ray detector take-off angle. For X-ray detector take-off angle, see "X-ray take-off angle" in ISO 23833.

4.7**signal processing**

subsequent treatment and modification of electrical signals leaving the detector by electronic means for further image processing and display

4.7.1**black level****dark level**

minimum output signal from the amplifier that corresponds to the darkest possible level on the screen

4.7.2**dynamic range**

difference between peak white and the black level

4.7.3**derivative processing**

method of enhancing selected spatial frequencies in an image

5 Terms and definitions used in SEM image formation and processing

5.1

scanning

action of obtaining time-controlled movement of the electron probe on the specimen surface with the synchronized movement of the spot on the display screen

5.1.1

area scanning

scanning in an x - y pattern to obtain an SEM image display

5.1.2

line scanning

scanning in a single (x or y) direction to obtain the display of the signal modulation

5.1.2.1

y modulation

operation of using the signal of intensity measured during the line scan to adjust the y deflection of the CRT to produce on the screen a curve displaying the distribution of intensity along the scan line

5.1.3

scanning distortion

loss of fidelity in a scanning image arising from defects in the scanning device or sometimes the scanning itself

5.1.3.1

Moiré effects

formation of Moiré fringes caused by the superposition of the periodicity of the specimen features and the grating of picture points forming the scanned image

5.2

SEM imaging

action of forming an image by a mapping operation that collects information from the specimen space and passes the information to the display space

5.2.1

analogue imaging

approach to SEM imaging in which the information collected from the specimen and the scanning control signal are treated and manipulated as continuous variables in the processing chain

5.2.2

digital imaging

approach to SEM imaging in which the information collected from the specimen and the scanning control signal are treated and manipulated as discrete variables, i.e. digitized in the processing chain, giving advantages over the analogue approach due to computer memory and data processing

5.2.2.1

digital resolution

number of discrete beam positions, i.e. the number of picture elements or "pixels"

EXAMPLE 512 × 512, 1 024 × 1 024.

5.2.2.2

intensity resolution

digital image depth

number of discrete levels in the digitized representation of the signal intensity, usually described as a power of 2

Note 1 to entry: 8 bits = 256 levels.

5.2.2.2.1**bit depth**
colour depth
pixel depth

maximum number of discrete levels available for the digitized representation of the signal intensity, represented as a power of 2

Note 1 to entry: See [5.2.2.2](#).

Note 2 to entry: The most common bit depths for SEM are: 8 bits, 12 bits, 16 bits, 24 bits and 32 bits. Scientific grey-scale images are typically 8-bit, 12-bit or 16-bit, providing 256, 4 096 or 64 536 discrete grey levels.

5.2.3**depth of field**

vertical distance required to bring the specimen from the optimum beam focus to a noticeably defocused position

5.2.4**picture element****pixel**

smallest discrete image data element that constitutes an SEM image

5.2.5**pixel size**

length of the pixel, measured at a specimen surface

Note 1 to entry: For a square or circular pixel, the horizontal and vertical pixel sizes should be the same.

5.3**contrast***C*

difference in signal between two arbitrarily chosen points (P_1 , P_2) of interest in the image field, normalized by the maximum possible signal available under the particular operating conditions

Note 1 to entry: Contrast is given by the equation

$$C = |S_2 - S_1| / S_{\max} \quad (0 < C < 1)$$

where

S_2 and S_1 are the signals of two arbitrarily chosen points (P_1 , P_2), respectively;

S_{\max} is the maximum possible signal available under the particular operating conditions.

5.3.1**atomic number contrast**

contrast that arises from a difference in the local chemical composition (atomic number or mass-fraction-averaged atomic number) within the specimen under study

5.3.2**channelling contrast**

contrast that arises from the electron channelling effect through different Bragg diffraction conditions in a crystallographic specimen under study

5.3.3**contrast components**

factors that influence the beam of electrons falling on the detector and thereby produce contrast in the specimen image

5.3.3.1

energy component

contrast component that arises when the contrast is carried by a certain portion of the electron energy distribution

5.3.3.2

number component

contrast component that arises as a result of different numbers of electrons leaving the specimen at different beam locations in response to changes in the specimen characteristics at those locations

5.3.3.3

trajectory component

contrast component that results from electrons leaving the specimen in different directions

5.3.4

crystallographic contrast

contrast that arises from electron channelling and diffraction as the result of interaction of beam electrons with the crystalline specimen

5.3.5

magnetic contrast

contrast that arises from interactions of the beam electrons with the magnetic field at the surface of or within the specimen

5.3.5.1

type 1 magnetic contrast

contrast that arises from interactions of the secondary electrons with the leakage magnetic field after they have exited the specimen surface

5.3.5.2

type 2 magnetic contrast

contrast that arises from the effect of the internal magnetic field upon the beam electrons as they initially scatter within the specimen

5.3.6

noise

time-varying disturbances superimposed on the analytical signal with fluctuations, leading to uncertainty in the signal intensity

Note 1 to entry: An accurate measure of noise can be determined from the standard deviation of the fluctuations. Visual or other estimates, such as peak-to-peak noise in a spectrum, may be useful as semiquantitative measures of noise.

Note 2 to entry: The fluctuations in the measured intensity can arise from a number of causes, such as statistical noise and electrical interference.

[SOURCE: ISO 18115-1:2013, definition 4.315]

5.3.7

Rose criterion

condition for an average observer to be able to distinguish small features in the presence of noise, which requires that the change in signal for the feature exceeds the noise by a factor of at least three

5.3.8

signal-to-noise ratio

ratio of signal to its noise

5.3.9

topographic contrast

contrast that arises from the difference in the local surface inclination of the specimen relative to the direction of the incident electron beam and to the position of the detector

5.3.9.1**surface tilt contrast**

main topographic contrast mechanism that arises from the difference in the local surface inclination of the specimen relative to the direction of the incident electron beam and to the position of the detector

5.3.10**voltage contrast**

contrast that arises from differences in surface potential from one location to another on the specimen

5.3.11**edge effect**

enhanced or reduced emission of secondary electrons at high-aspect-ratio surface features

Note 1 to entry: The effect is dependent upon the interaction volume and the mean escape depth of secondary electrons from that volume as a function of beam position.

5.4**image distortion**

loss of fidelity of dimensions in the SEM image

5.4.1**projection distortion**

distortion that arises from the equivalent geometric projection effect on the SEM image when using a scan generated by rocking about a point on the central optic axis perpendicular to the specimen surface

5.4.1.1**gnomonic distortion**

projection distortion that arises from the non-linear increment of the scan displacement with the scan angle from the central optic axis

5.4.1.2**foreshortening distortion**

projection distortion that results from the tilt of a flat surface or randomly tilted facets of a specimen

5.5**analogue image processing**

operation of treating and manipulating the image-information-carrying signals as continuously varying quantities

5.6**digital image processing**

operation in which the image-information-carrying signals are treated and manipulated as discrete variables, i.e. digitized

5.6.1**digital image enhancement**

category of digital image processing which seeks to render information in the image more readily visible to the operator

5.6.2**frame integration**

mode of "real-time" image processing, using a *frame store* (5.6.3), which accumulates several incoming image frames, acquired at TV rates or at slower scan speeds, and integrates them to form a final mean image

5.6.3**buffer store****frame store**

special dedicated computer memory board consisting of an array of memory registers adequate for temporarily storing the data of one or more images

5.6.4

graphics file format image file format

archival digital format for storing the contents of the frame store

Note 1 to entry: The most popular image file formats are: bitmap (BMP), graphics interchange format (GIF), tagged image format (TIF) and joint photographic experts group (JPG). The TIF format is the scientific format that preserves all data and keeps the size of each pixel in its header. Consequently, this format is preferred to maintain the integrity of the images.

6 Terms and definitions used in SEM image interpretation and analysis

6.1

light-optical analogue

strong correspondence of the SEM imaging process using a positively biased E-T detector to the normal human vision process for scenes with illumination from above

6.2

electron beam induced current

EBIC

current that is induced in specimens of semiconductor material or semiconductor devices by electron beam bombardment

6.2.1

β -conductivity

conductivity, such as the charge collection current, that exhibits variation in the absence of any electron voltaic effect

6.2.2

charge collection current

current that flows round a circuit connecting two contacts to the specimen in the EBIC condition

6.2.3

electron voltaic effect

generation of an electromotive force in the specimen, thus driving the charge collection current round an external circuit

6.2.4

specimen current

absorbed current

current flowing between the conducting specimen and ground

Note 1 to entry: It represents the difference between the beam current injected into the specimen and the current emitted as backscattered electrons and secondary electrons.

6.3

Bragg diffraction relation

mathematical expression which relates the wavelength of the incident radiation and the spacing of the atomic planes of a crystal to the angles, between the radiation beam and the atomic planes, at which diffraction takes place

Note 1 to entry: The mathematical expression is

$$n\lambda = 2d\sin\theta$$

where

d is the spacing of the atomic planes;

n is an integer;